	Type	Ilits	Search Text	DBs	Time Stamp
ı	IS&R	10118	(257/621.675,685,686,698,699,708,712.713,717,723,735,737,777,778).CCLS.	USPAT	2008/01/22 10:55
24	IS&R	8361	(257/621,675,685,686,698,699,708,712,713,717,723,735,737,777,778).CCLS.	JPO: DERWENT: IBM-TDH	2008/01/22 15:35
3	BRS	145	tadhesive bonding) with (epoxy adj resin) same (heat adj (sink radiation radiator))	USPAT	2008/02/04 04:35
4	BRS	158	(adhesive bonding) with (epoxy adj resin) same (heat adj (sink radiation radiator))	US-PGPUB: USOCR: FPRS, EPO; JPO; DERWENT; IBM, TDB	2008/02/04 04.36
5	BRS	400	stack\$5 near3 (chip die device) and (adhesive adhesion bond bonding) and (protective passivation) and (heat adj (sink radiation radiator))	USPAT	2008/02/64 64:39
85	BRS	7	stack\$5 near3 (chip die device) and (adhesive adhesion bond bonding) and (protective passivation) and (heat adj (sink radiation radiator))	US-PGPUB; USOCR; I-PRS; EPO; IPO; DERWENT; IBM_TDB	2008/02/04 04:56
7	BRS	, des	(stack\$5 near3 (chip die slevice) and (adhesive adhesion bond bonding) and (protective passivation) and (freat adj (sink radiation radiator)) and (thick thickness)).chm.	US-PGPUB	2008/02/04 05:08
8	BRS	3248	(heat adj (sink radiation radiator)) with (thick thickness)	USPAT	2008/02/04 08:45
9	BRS	(073	(heat adj (sink radiation radiator)) near3 (thick thickness)	USPAT	2668/02/04 08:46
10	BRS	37	theat adj (sink radiation radiator)) near3 (thick thickness) and (stack\$5 near3 (chip die device))	USPAT	2008/02/04 08:46
***	BRS	53	Theat adj (sink radiation radiator)) near3 (thick Thickness) and (stock\$5 near3 (chip die device))	USPAT	2008/02/04

	Турс	Hits	Search Text	DBs	Time Stamp
12	BSKS	57	(heat adj (sink radiation radiator)) near3 (thick thickness) and (stack\$5 near) (chip die device))	LIS-POPUB: USOCK: FPRS; EPO; IPO; DERWENT, IBM_TDB	2008/02/04 08:57
13	BRS	8	((heat adj (sink radiation radiator)) and (thick thickness) and (stack\$5 near3 (chip die device)) and (insulating insulation dielectric) and stack\$5),clm.	US-PGPUB	2668/02/04 09:19